

ABSTRACT

A method of making a diode structure includes the step of depositing a transparent electrode layer of any one or more of the group ZnO, ZnS and CdO onto a substrate layer, and depositing an active semiconductor junction having an n-type layer
5 and a p-type layer onto the transparent electrode layer under process conditions that avoid substantial degradation of the electrode layer. A back electrode coating layer is applied to form a diode structure.